

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

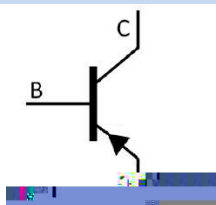
/ Features

Low collector saturation voltage, high speed switching time, complementary to, KTC2814.

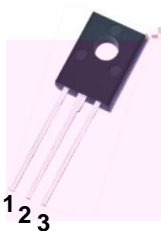
/ Applications

Power amplifier application, power switching application.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

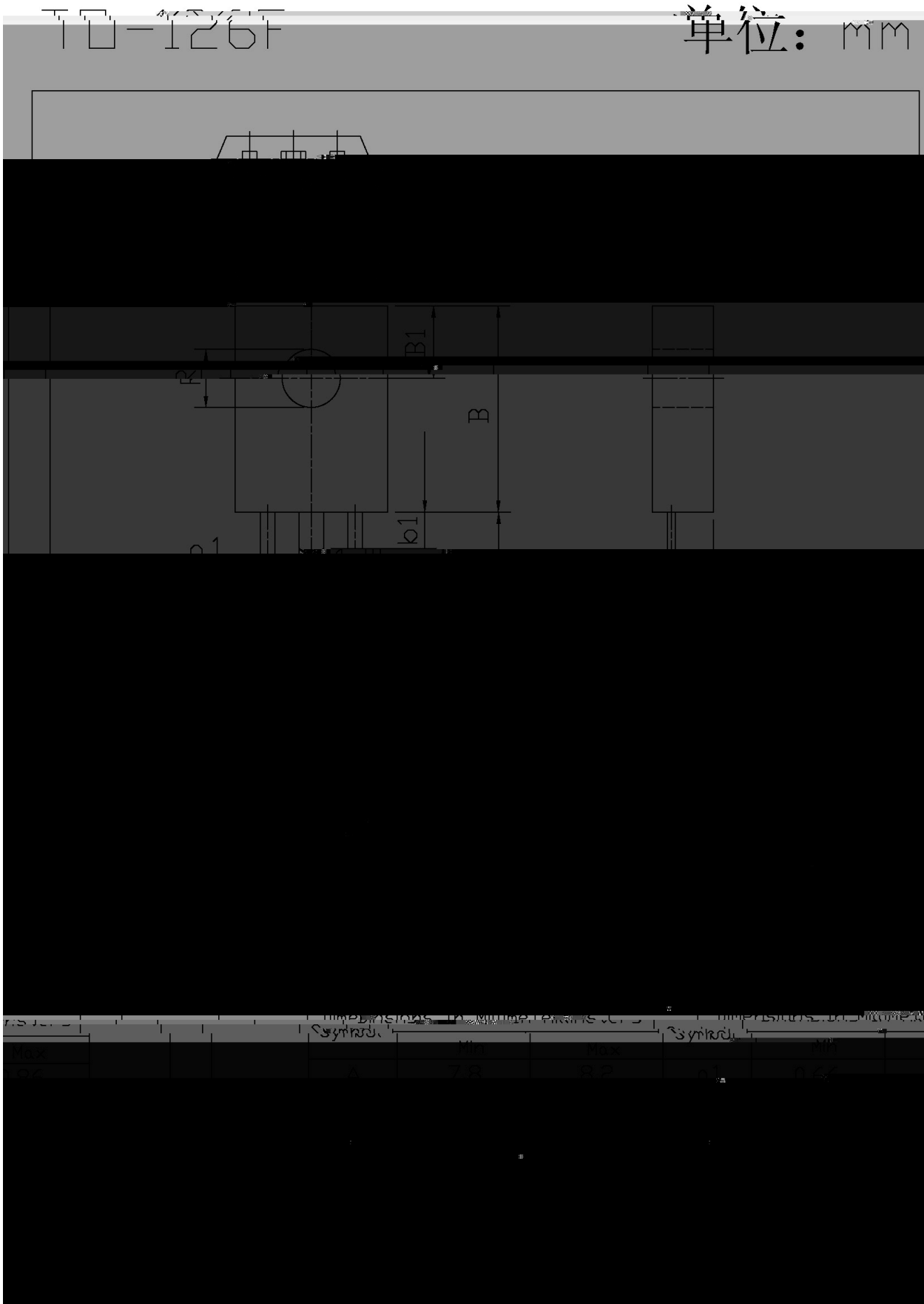
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_C=25 \text{ }^\circ\text{C})$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C				

/ Package Dimensions



/ Marking Instructions



BR

A1715

Note:

BR: Company Code

A1715: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



1	25 150	60 90sec;	Note: 1.Preheating:25~150 , Time:60~90sec.
2	255±5	5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm ³)
--------------	-------	-----------	-------------------------